FÃ©lix L MartÃ-nez

List of Publications by Year
in descending order

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46	764	623734	552781
papers	citations	14 h-index	26 g-index

46	46	46	896
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Compact Double Notch Coplanar and Microstrip Bandstop Filters Using Metamaterialâ€"Inspired Open Ring Resonators. Electronics (Switzerland), 2021, 10, 330.	3.1	5
2	Design of high-performance microstrip and coplanar low-pass filters based on electromagnetic bandgap (EBG) structures. AEU - International Journal of Electronics and Communications, 2020, 123, 153311.	2.9	11
3	Teaching-learning model for the science of electronics. Journal of Technology and Science Education, 2020, 10, 87.	1.2	1
4	Reconfigurable Coplanar Waveguide (CPW) and Half-Mode Substrate Integrated Waveguide (HMSIW) Band-Stop Filters Using a Varactor-Loaded Metamaterial-Inspired Open Resonator. Materials, 2018, 11, 39.	2.9	6
5	Compact Bandstop Half-Mode Substrate Integrated Waveguide Filter Based on a Broadside-Coupled Open Split-Ring Resonator. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 3001-3010.	4.6	15
6	Tunable ferroelectrics for frequency agile microwave and THz devices. , 2018, , 251-264.		1
7	Electronically tunable microstrip bandstop filters using a varactor-loaded open ring resonator (VLORR). Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	4
8	Half mode substrate integrated waveguide (HMSIW) notch filters using open ring resonators. , 2017, , .		1
9	Modified split-ring resonator for microstrip dual- band notch filter. , 2015, , .		4
10	Substrate Integrated Waveguide (SIW) With Koch Fractal Electromagnetic Bandgap Structures (KFEBG) for Bandpass Filter Design. IEEE Microwave and Wireless Components Letters, 2015, 25, 160-162.	3.2	21
11	Optimisation of chirped and tapered microstrip Koch fractal electromagnetic bandgap structures for improved lowâ€pass filter design. IET Microwaves, Antennas and Propagation, 2015, 9, 889-897.	1.4	14
12	A flat-passband and wide-stopband low-pass filter based on tapered Cauchy microstrip Koch fractal EBG structure. , 2014, , .		2
13	Ambient assisted living system with capacitive occupancy sensor. Expert Systems, 2014, 31, 378-388.	4.5	11
14	Low-Frequency CMOS Bandpass Filter for PIR Sensors in Wireless Sensor Nodes. IEEE Sensors Journal, 2014, 14, 4085-4094.	4.7	14
15	EMFi-based low-power occupancy sensor. Sensors and Actuators A: Physical, 2013, 191, 78-88.	4.1	8
16	An energy efficient middleware for an ad-hoc AAL wireless sensor network. Ad Hoc Networks, 2013, 11, 907-925.	5.5	8
17	Dielectric constant tunability at microwave frequencies and pyroelectric behavior of lead-free submicrometer-structured (Bi_{0.5}Na_{0.5})_{1-x}Ba_xTiO₃ ferroelectric ceramics. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2013, 60, 1595-1602.	3.0	17
18	Pyroelectric and dielectric properties of ferroelectric ceramics for microwave tunable devices and infrared detector applications. , 2012, , .		1

#	Article	IF	Citations
19	A fourth order CMOS band pass filter for PIR sensors. , 2012, , .		2
20	A system for ubiquitous fall monitoring at home via a wireless sensor network and a wearable mote. Expert Systems With Applications, 2012, 39, 5566-5575.	7.6	55
21	Novel Compact Wide-Band EBG Structure Based on Tapered 1-D Koch Fractal Patterns. IEEE Antennas and Wireless Propagation Letters, 2011, 10, 1104-1107.	4.0	20
22	1D Koch fractal electromagnetic bandgap microstrip structures with r/a ratios higher than 0.5. Microwave and Optical Technology Letters, 2011, 53, 646-649.	1.4	11
23	Physical properties of high pressure reactively sputtered hafnium oxide. Vacuum, 2008, 82, 1391-1394.	3.5	11
24	High-pressure reactively sputtered HfO2: Composition, morphology, and optical properties. Journal of Applied Physics, 2007, 102, .	2.5	33
25	Optical properties and structure of HfO₂thin films grown by high pressure reactive sputtering. Journal Physics D: Applied Physics, 2007, 40, 5256-5265.	2.8	156
26	Compositional analysis of polycrystalline hafnium oxide thin films by heavy-ion elastic recoil detection analysis. Thin Solid Films, 2006, 515, 695-699.	1.8	4
27	Bonding structure and hydrogen content in silicon nitride thin films deposited by the electron cyclotron resonance plasma method. Thin Solid Films, 2004, 459, 203-207.	1.8	27
28	Microstructural modifications induced by rapid thermal annealing in plasma deposited SiOxNyHz films. Journal of Applied Physics, 2003, 94, 1019-1029.	2.5	9
29	Optical and structural properties of SiOxNyHz films deposited by electron cyclotron resonance and their correlation with composition. Journal of Applied Physics, 2003, 93, 8930-8938.	2.5	21
30	Rapid thermally annealed plasma deposited SiNx:H thin films: Application to metalâ€“insulatorâ€“semiconductor structures with Si, In0.53Ga0.47As, and InP. Journal of Applied Physics, 2003, 94, 2642-2653.	2.5	14
31	Characterization of nitrogen-rich silicon nitride films grown by the electron cyclotron resonance plasma technique. Semiconductor Science and Technology, 2003, 18, 633-641.	2.0	17
32	Rapid thermal annealing effects on the electrical behavior of plasma oxidized silicon/silicon nitride stacks gate insulators. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1306.	1.6	9
33	Composition and optical properties of silicon oxynitride films deposited by electron cyclotron resonance. Vacuum, 2002, 67, 507-512.	3.5	40
34	Physical properties of plasma deposited SiOx thin films. Vacuum, 2002, 67, 525-529.	3.5	11
35	Rapid thermal annealing effects on plasma deposited SiOx:H films. Vacuum, 2002, 67, 531-536.	3.5	10
36	Temperature effects on the electrical properties and structure of interfacial and bulk defects in Al/SiNx:H/Si devices. Journal of Applied Physics, 2001, 90, 1573-1581.	2.5	15

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37	Lattice recovery by rapid thermal annealing in Mg+-implanted InP assessed by Raman spectroscopy. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 252-256.	1.4	6
38	Electrical properties of rapid thermally annealed SiNx:H/Si structures characterized by capacitance-voltage and surface photovoltage spectroscopy. Semiconductor Science and Technology, 2001, 16, 534-542.	2.0	8
39	Molecular models and activation energies for bonding rearrangement in plasma-depositedaâˆ¼SiNx:Hdielectric thin films treated by rapid thermal annealing. Physical Review B, 2001, 63, .	3.2	38
40	Compositional analysis of amorphous SiNx: H films by ERDA and infrared spectroscopy. Surface and Interface Analysis, 2000, 30, 534-537.	1.8	13
41	Defect structure of SiNx:H films and its evolution with annealing temperature. Journal of Applied Physics, 2000, 88, 2149-2151.	2.5	21
42	Effect of substrate temperature in SiOxNy films deposited by electron cyclotron resonance. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1263-1268.	2.1	15
43	Photovoltage effects under sinusoidal illumination. Journal of Applied Physics, 1999, 86, 3469-3471.	2.5	0
44	Fabrication and characterisation of thin low-temperature MBE-compatible silicon oxides of different stoichiometry. Thin Solid Films, 1999, 349, 135-146.	1.8	11
45	Optical absorption in amorphous hydrogenated silicon nitride thin films deposited by the electron cyclotron resonance plasma method and subjected to rapid thermal annealing. Thin Solid Films, 1999, 343-344, 433-436.	1.8	2
46	Influence of rapid thermal annealing processes on the properties of SiN :H films deposited by the electron cyclotron resonance method. Journal of Non-Crystalline Solids, 1998, 227-230, 523-527.	3.1	41